DOCUMENT CHANGE REQUEST

DCR number 790	Changes required for: General	Originator: Samuel Savin
Date: 2013/09/30	Date sent: 2013/04/24	Organisation: STMicroelectronics
Status: IMPLEMENTED		

Title:	TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH8N10		
Number:	5205/023	Issue:	2

Other documents affected:

Page:

Paragraph:

Original wording:

Proposed wording:

Justification:

Delete the TO-39, this package does not meet of customer expectations (no space market demand). ST has not manufactured and sold any products in this version (TO-39).

A Contrary the SMD.5 is requested, the ESCC qualification has been done according this package and also from new silicon for which the thickness of the gate oxide is 470Å instead of 350Å on the previous one meaning a review of the limits (mainly AC test parameters).

Attachments:

strh8n10_dcr_revision_2.pdf, strh8n10_dcr_revision_2.docx, null

Modifications:

The following additions and amendments to the original DCR attachment shall apply:

Amendment: Para 1.4.2 replace with following (modified) text:
Delete Variant 02 and amend variant 01 to be as follows:
• Variant Number: 01
• Based on Type: STRH8N10
• Case: SMD.5
• Terminal material and Finish: Q14
• Weight max g: 2
• Total dose Radiation Level Letter: F [50kRAD/Si]

The terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

Addition: Para 1.5 Power Dissipation
Amend max rating to be 62.5W (was 25W)

Addition: Para 1.8
Amend item b) to read Terminals (was leads).

Addition (& clarification): Para 2.1.1.2
Add Para 2.1.1.2 as follows:
Deviations from Qualification and Periodic Testing - Chart F3
- Constant Acceleration is not applicable (for SMD.5).
- Terminal Strength is not applicable (for SMD.5).

Amendment: Para 2.4 Terminal Strength
Delete Para. 2.4 (& renumber subsequent Paras. accordingly)

Amendment: Para 2.11.2
Amendment per note “a)” under the table is deleted from this DCR.

Approval signature:



Date signed:

2013-09-30